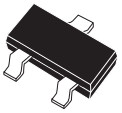
查询CMPT918供应商

CMPT918

NPN SILICON RF TRANSISTOR



SOT-23 CASE

Central™
Semiconductor Corp.

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMPT918 type is an NPN silicon RF transistor manufactured by the epitaxial planar process, epoxy molded in a surface mount package, designed for high frequency (VHF/UHF) amplifier and oscillator applications.
Marking code is C3B.

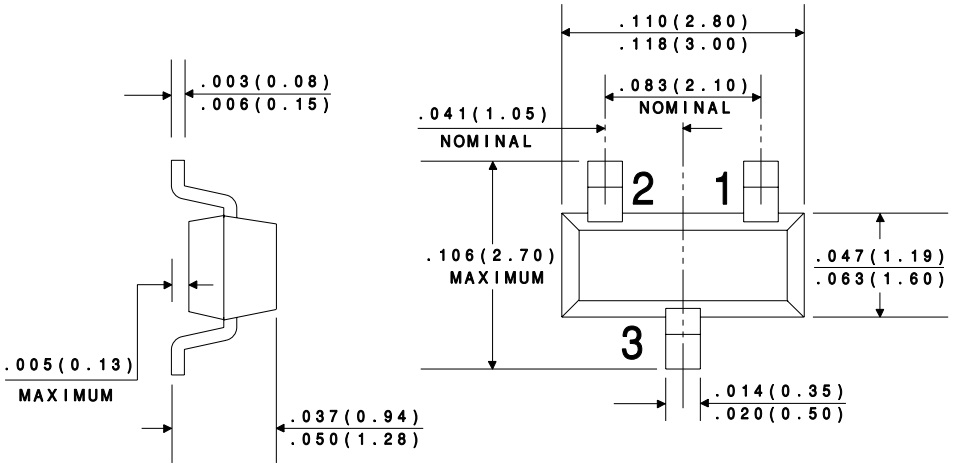
MAXIMUM RATINGS (T_A=25°C)

	SYMBOL		UNITS
Collector-Base Voltage	V_{CBO}	30	V
Collector-Emitter Voltage	V_{CEO}	15	V
Emitter-Base Voltage	V_{EBO}	3.0	V
Collector Current	I_C	50	mA
Power Dissipation	P_D	350	mW
Operating and Storage Junction Temperature	T_J,T_{stg}	-65 to +150	°C
Thermal Resistance	Θ_{JA}	357	°C/W

ELECTRICAL CHARACTERISTICS (T_A=25°C unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNITS
I_{CBO}	V_{CB}=15V		10	nA
BV_{CBO}	I_C=1.0μA	30		V
BV_{CEO}	I_C=3.0mA	15		V
BV_{EBO}	I_E=10μA	3.0		V
$V_{CE(SAT)}$	I_C=10mA, I_B=1.0mA		0.4	V
$V_{BE(SAT)}$	I_C=10mA, IB=1.0mA		1.0	V
h_{FE}	V_{CE}=1.0V, I_C=3.0mA	20		
f_T	V_{CE}=10V, I_C=4.0mA, f=100MHz	600		MHz
C_{ob}	V_{CB}=0V, I_E=0, f=1.0MHz		3.0	pF
C_{ob}	V_{CB}=10V, IE=0, f=1.0MHz		1.7	pF
C_{ib}	V_{EB}=0.5V, I_C=0, f=1.0MHz		2.0	pF
P_{out}	V_{CB}=15V, I_C=8.0mA, f=500MHz	30		mW
G_{pe}	V_{CB}=12V, I_C=6.0mA, f=200MHz	11		dB
NF	V_{CE}=6.0V, I_C=1.0mA, R_S=50Ω, f=60MHz		6.0	dB

All dimensions in inches (mm).



LEAD CODE:

1) BASE
2) EMITTER
3) COLLECTOR

R2